

深圳市晶泰源电子有限公司

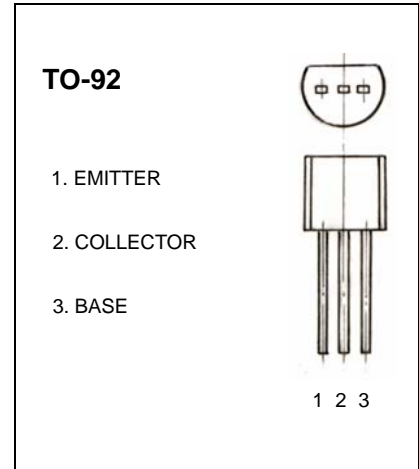
2SA608 TRANSISTOR (PNP)

FEATURES

- Capable of being used in the low frequency to high frequency range.
- Large current capacity and wide ASO.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-100	mA
P_C	Collector Power Dissipation	400	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}$, $I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$, $I_B=0$	-30			V
Emitter-Base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}$, $I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-25\text{V}$, $I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}$, $I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-6\text{V}$, $I_C=-1\text{mA}$	60		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}$, $I_B=-5\text{mA}$			-0.5	V
Transition frequency	f_T	$V_{CE}=-6\text{V}$, $I_C=-10\text{mA}$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-6\text{V}$, $f=1\text{MHz}$		7		pF

CLASSIFICATION OF h_{FE}

Rank	D	E	F	G
Range	60-120	100-200	160-320	280-560